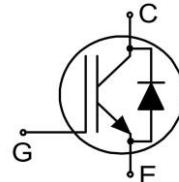


■ Description

The 025R135F47 is inverse conduction type insulated gate bipolar transistor adopts the new generation of inverse conduction type (Reverse Conducting) channel grid field cut-off process, which has the characteristics of low conduction loss and switching loss, high breakdown voltage, internal integrated continuous flow diode, positive temperature coefficient such as Inductive cooking, Inverterized microwave ovens, etc.



■ Preliminary Data

V _{CES}	I _C	V _{CE(sat)}	V _F	Package
1350V	25A	1.97V	2.5V	TO-247

■ Features

- ✓ Advanced Trench Field stop Technology
- ✓ Ultra low V_{CE(sat)} and switching loss
- ✓ High Energy Efficiency, Temperature Stability
- ✓ Easy Parallel Switching Capability due to Positive

Temperature Coefficient in V_{CE(sat)}

■ Application

- ✓ Inductive cooking
- ✓ Inverterized microwave ovens

■ Absolute Maximum Ratings (T_c=25°C, unless otherwise specified.)

Parameter	Symbol	Rating	Unit
Collector-emitter Voltage	V _{CES}	1350	V
Transient Gate-emitter Voltage	V _{GES}	±20	V
Continuous Drain Current	T _c =25°C	I _C	A
	T _c =100°C		
Pulsed Collector Current, Limited by T _{jmax}	I _{CM}	75	A
Diode Continuous Collector Current	T _c =25°C	I _F	A
	T _c =100°C		
Diode Pulsed Current, Limited by T _{jmax}	I _{FM}	75	A
Power Dissipation	T _c =25°C	P _{tot}	W
	T _c =100°C		
Operating Junction Temperature Range	T _j	-40~150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

■ Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
IGBT Thermal Resistance, Junction-to-Case	R_{thJC}	-	-	0.55	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient		-	-	40	

■ Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise specified.)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics						
Collector-emitter Breakdown Voltage	BV_{CES}	$\text{V}_{\text{GE}}=0\text{V}, \text{I}_{\text{CE}}=1\text{mA}$	1350	-	-	V
Gate Threshold Voltage	$\text{V}_{\text{GE}(\text{th})}$	$\text{V}_{\text{CE}}=\text{V}_{\text{GE}}, \text{I}_{\text{C}}=250\text{uA}$	4.6	5.5	7.4	V
Collector-emitter saturation voltage	$\text{V}_{\text{CE}(\text{sat})}$	$\text{V}_{\text{GE}}=15\text{V}, \text{I}_{\text{C}}=25\text{A}$	-	1.97	2.62	V
Zero Gate Voltage Collector Current	I_{CES}	$\text{V}_{\text{CE}}=1350\text{V}, \text{V}_{\text{GE}}=0\text{V}$	-	-	750	uA
Gate-emitter Leakage Current	I_{GESF}	$\text{V}_{\text{GE}}=20\text{V}, \text{V}_{\text{GE}}=0\text{V}$	-	-	250	nA
	I_{GESR}	$\text{V}_{\text{GE}}=-20\text{V}, \text{V}_{\text{GE}}=0\text{V}$	-	-	-250	
Dynamic Characteristics						
Input Capacitance	C_{ies}	$\text{V}_{\text{CE}}=30\text{V}, \text{V}_{\text{GE}}=0\text{V}, \text{f}=1\text{MHz}$	-	2210	-	pF
Output Capacitance	C_{oes}		-	52	-	
Reverse Transfer Capacitance	C_{res}		-	40	-	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$\text{V}_{\text{CE}}=600\text{V}, \text{I}_{\text{C}}=25\text{A}, \text{R}_{\text{G}}=10\Omega, \text{V}_{\text{GE}}=15\text{V}, \text{T}_J=25^{\circ}\text{C}$	-	31	-	ns
Rise Time	t_{r}		-	33	-	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		-	191	-	
Fall Time	t_{f}		-	69	-	
Turn-on energy	E_{on}		-	1.76	-	mJ
Turn-off energy	E_{off}		-	0.92	-	
Gate Charge Characteristics						
Gate to Emitter Charge	Q_{ge}	$\text{V}_{\text{CC}}=960\text{V}, \text{I}_{\text{C}}=25\text{A}, \text{V}_{\text{GE}}=0\sim 15\text{V}$	-	20	-	nC
Gate to Collector Charge	Q_{gc}		-	71	-	
Gate Charge Total	Q_{g}		-	138	-	
Reverse Diode Characteristics						
Diode forward voltage	V_{F}	$\text{V}_{\text{GE}}=0\text{V}, \text{I}_{\text{F}}=25\text{A}$	-	2.5	3.3	V

■ Typical Electrical Characteristics

Figure 1 Output Characteristics

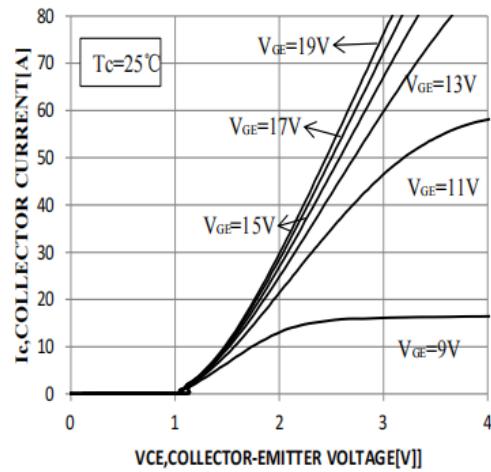


Figure 2 Output Characteristics

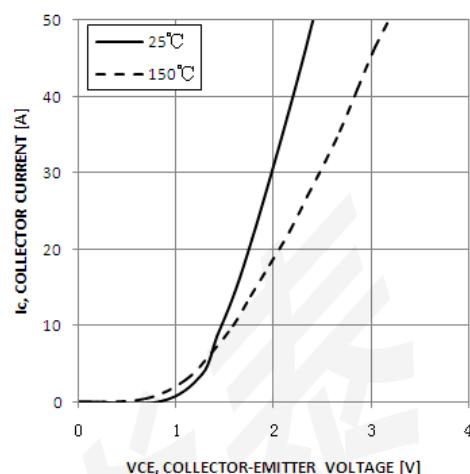


Figure 3 Gate Charge Wave Form

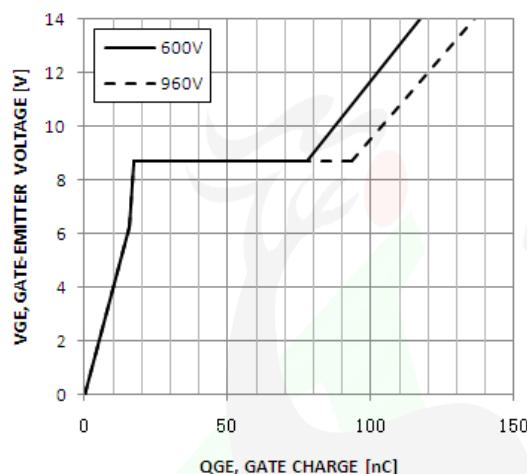


Figure 4 Capacitance Characteristics

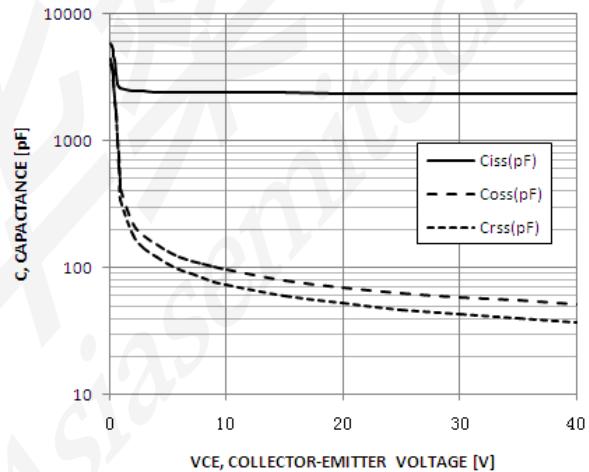


Figure 5 Switching Loss vs. R_g

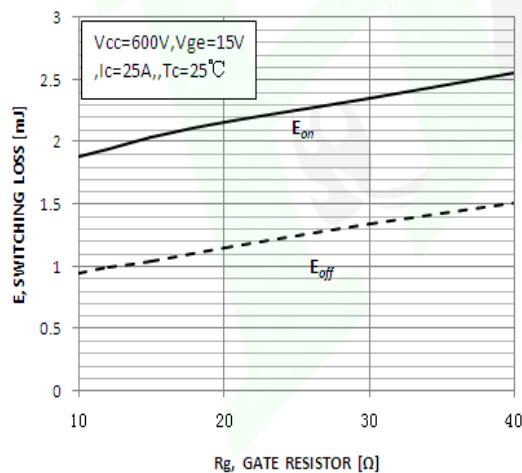


Figure 6 Switching Loss vs. Collector Current

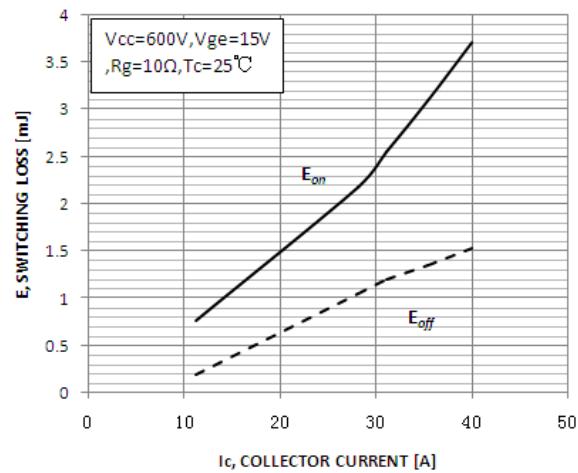
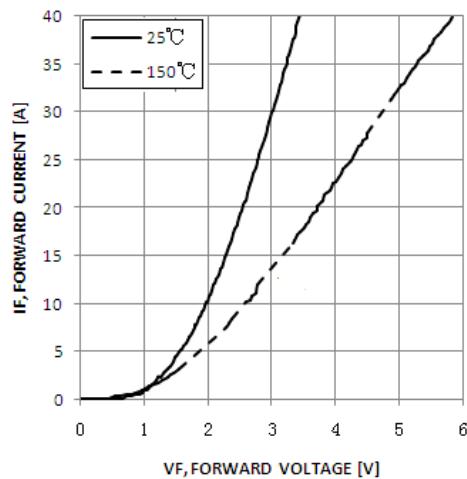
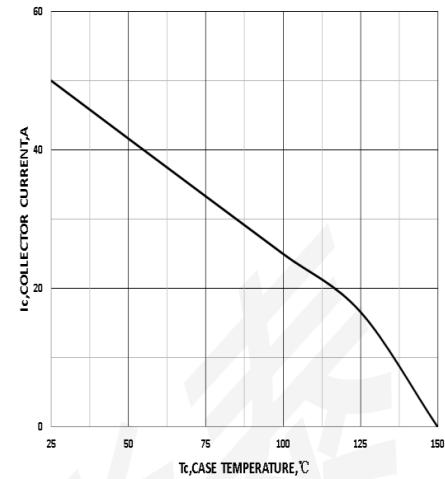
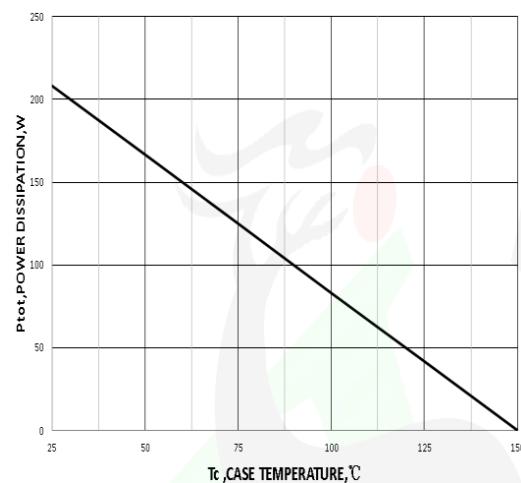
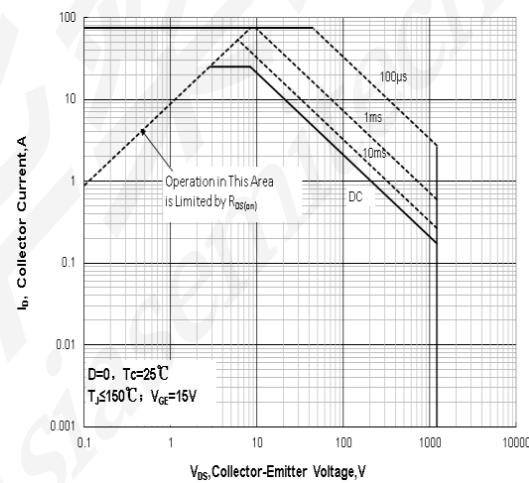
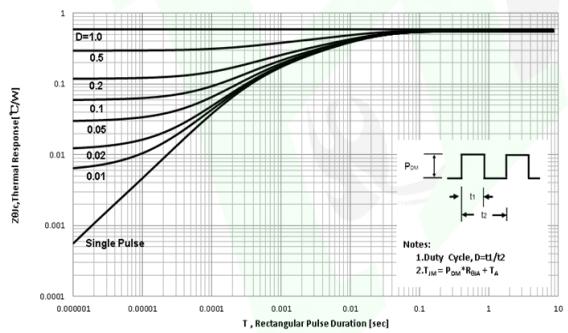
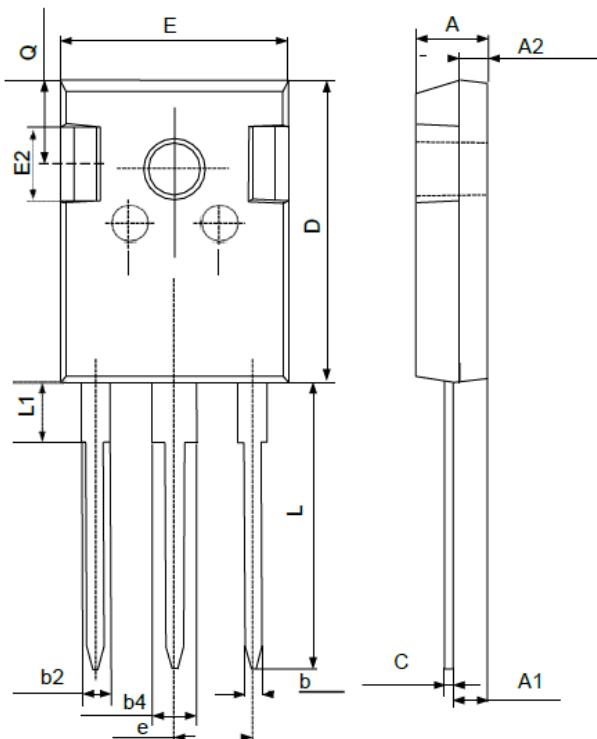


Figure 7 Forward Characteristics**Figure 8 Collector Current vs. Case Temperature****Figure 9 P_{tot} vs. Case Temperature****Figure 10 Forward Bias Safe Operating Area****Figure 11 Transient thermal impedance IGBT****Figure 18. IGBT Transient Thermal Impedance**

■ Package outlines

SYMBOL	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	---	1.36
b2	1.91	---	2.25
b4	2.91	---	3.25
c	0.51	---	0.75
D	20.80	21.00	21.30
E	15.50	15.80	16.10
E2	4.40	5.00	5.20
e	5.44 BSC		
L	19.72	19.92	20.22
L1	---	---	4.30
Q	5.60	5.80	6.00

■ Disclaimer

The product manual contains basic data and scope of application. The technician must evaluate the product data and use the product correctly.

All information in the specification is true and reliable. If you have any out-of-specification requirements for product data or have any questions about our products, please contact the sales office responsible for you.

Our products are prohibited from being used in illegal and criminal activities that endanger health and national interests.